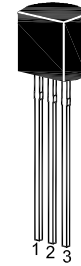


2SC2362

NPN Silicon Epitaxial Planar Transistor

High voltage low noise amplifier applications

The transistor is subdivided into three groups F, G and H, according to its DC current gain.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	120	V
Collector Emitter Voltage	V_{CEO}	100	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	50	mA
Collector Current (Pulse)	I_{CP}	100	mA
Collector Dissipation	P_{tot}	400	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 6\text{ V}$, $I_C = 1\text{ mA}$ Current Gain Group	F h_{FE}	160	-	320	-
	G h_{FE}	280	-	560	-
	H h_{FE}	480	-	960	-
Collector Base Cutoff Current at $V_{CB} = 80\text{ V}$	I_{CBO}	-	-	1	μA
Emitter Base Cutoff Current at $V_{EB} = 4\text{ V}$	I_{EBO}	-	-	1	μA
Collector Base Breakdown Voltage at $I_C = 10\text{ }\mu\text{A}$	$V_{(BR)CBO}$	120	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	100	-	-	V
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$	$V_{CE(sat)}$	-	-	0.5	V
Gain Bandwidth Product at $V_{CE} = 6\text{ V}$, $I_C = 1\text{ mA}$	f_T	-	130	-	MHz
Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	1.8	-	pF
Noise Level at $V_{CC} = 30\text{ V}$, $I_C = 1\text{ mA}$, $R_g = 56\text{ K}\Omega$, $V_G = 77\text{ dB}/1\text{ KHz}$	$C_{NO(ave)}$	-	-	35	mV
Noise Peak Level at $V_{CC} = 30\text{ V}$, $I_C = 1\text{ mA}$, $R_g = 56\text{ K}\Omega$, $V_G = 77\text{ dB}/1\text{ KHz}$	$C_{NO(peak)}$	-	-	200	mV

